

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π -MOSIII)

2SK2718

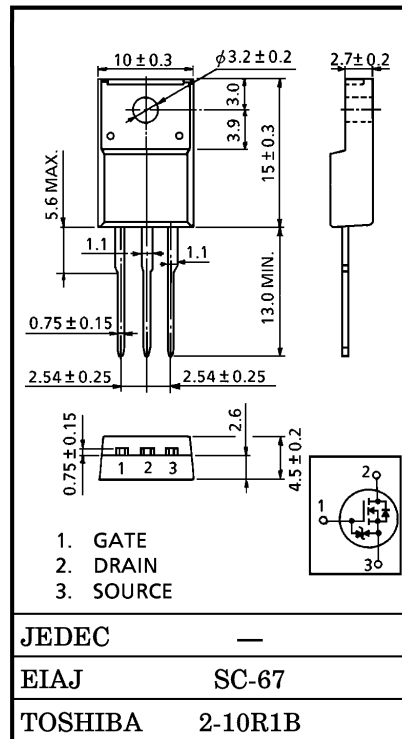
HIGH SPEED, HIGH CURRENT SWITCHING APPLICATIONS
DC-DC CONVERTER AND MOTOR DRIVE APPLICATIONS

INDUSTRIAL APPLICATIONS
Unit in mm

- Low Drain-Source ON Resistance : $R_{DS(ON)} = 5.6\Omega$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = 2.0S$ (Typ.)
- Low Leakage Current : $I_{DSS} = 100\mu A$ (Max.) ($V_{DS} = 720V$)
- Enhancement-Mode : $V_{th} = 2.0 \sim 4.0V$ ($V_{DS} = 10V, I_D = 1mA$)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT	
Drain-Source Voltage	V_{DSS}	900	V	
Drain-Gate Voltage ($R_{GS} = 20k\Omega$)	V_{DGR}	900	V	
Gate-Source Voltage	V_{GSS}	± 30	V	
Drain Current	DC	I_D	2.5	A
	Pulse	I_{DP}	7.5	A
Drain Power Dissipation ($T_c = 25^\circ C$)	P_D	40	W	
Single Pulse Avalanche Energy**	E_{AS}	216	mJ	
Avalanche Current	I_{AR}	2.5	A	
Repetitive Avalanche Energy*	E_{AR}	4.0	mJ	
Channel Temperature	T_{ch}	150	$^\circ C$	
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$	



JEDEC	—
EIAJ	SC-67
TOSHIBA	2-10R1B

Weight : 1.9g

Thermal Characteristics

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Case	$R_{th(ch-c)}$	3.125	$^\circ C / W$
Thermal Resistance, Channel to Ambient	$R_{th(ch-a)}$	62.5	$^\circ C / W$

Note ;

* Repetitive rating ; Pulse Width Limited by Max. junction temperature.

** $V_{DD} = 90V$, Starting $T_{ch} = 25^\circ C$, $L = 63.4mH$
 $R_G = 25\Omega$, $I_{AR} = 2.5A$ (See Figure)

**This transistor is an electrostatic sensitive device.
Please handle with caution.**

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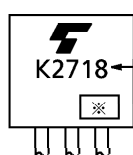
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		IGSS	VGS = ±25V, VDS = 0V	—	—	±10	μA
Gate-Source Breakdown Voltage		V (BR) GSS	IG = 10μA, VDS = 0V	±30	—	—	V
Drain Cut-off Current		IDSS	VDS = 720V, VGS = 0V	—	—	100	μA
Drain-Source Breakdown Voltage		V (BR) DSS	ID = 10mA, VGS = 0V	900	—	—	V
Gate Threshold Voltage		Vth	VDS = 10V, ID = 1mA	2.0	—	4.0	V
Drain-Source ON Resistance		RDS (ON)	VGS = 10V, ID = 1.5A	—	5.6	6.4	Ω
Forward Transfer Admittance		Yfs	VDS = 20V, ID = 1.5A	1.0	2.0	—	S
Input Capacitance		Ciss	VDS = 25V, VGS = 0V f = 1MHz	—	510	—	pF
Reverse Transfer Capacitance		Crss		—	10	—	
Output Capacitance		Coss		—	55	—	
Switching Time	Rise Time	tr		—	20	—	ns
	Turn-on Time	ton		—	60	—	
	Fall Time	tf		—	40	—	
	Turn-off Time	toff		VIN : tr, tf < 5ns Duty ≤ 1%, tw = 10μs	—	115	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Qg	VDD ≐ 400V, VGS = 10V, ID = 2.5A	—	21	—	nC
Gate-Source Charge		Qgs		—	11	—	
Gate-Drain ("Miller") Charge		Qgd		—	10	—	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	IDR	—	—	—	2.5	A
Pulse Drain Reverse Current	IDRP	—	—	—	7.5	A
Diode Forward Voltage	VDSF	IDR = 2.5A, VGS = 0V	—	—	—2.0	V
Reverse Recovery Time	t _{rr}	IDR = 2.5A, VGS = 0V	—	960	—	ns
Reverse Recovery Charge	Q _{rr}	dIDR / dt = 100A / μs	—	5.3	—	μC

MARKING



TYPE

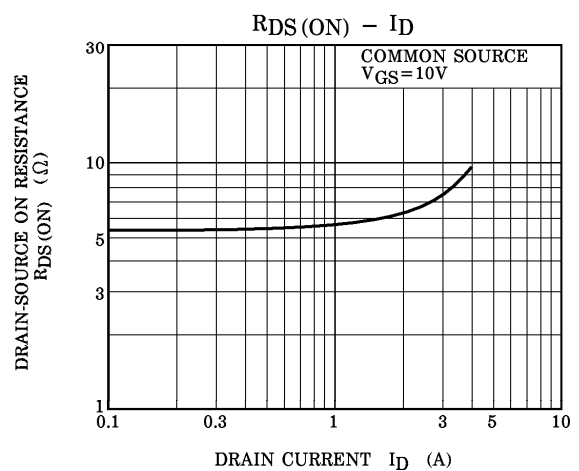
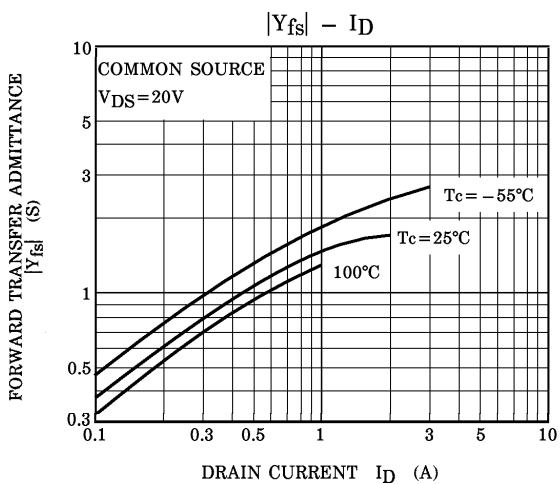
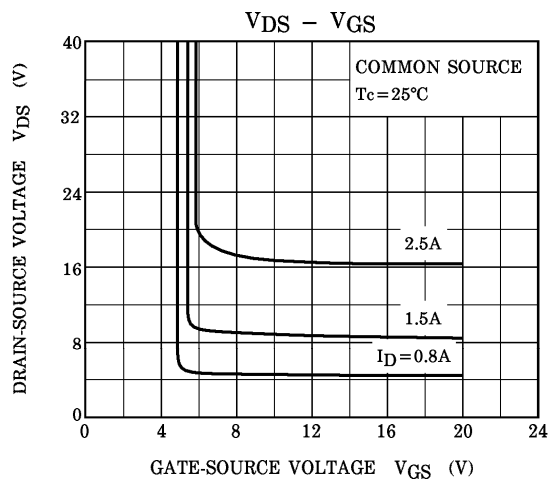
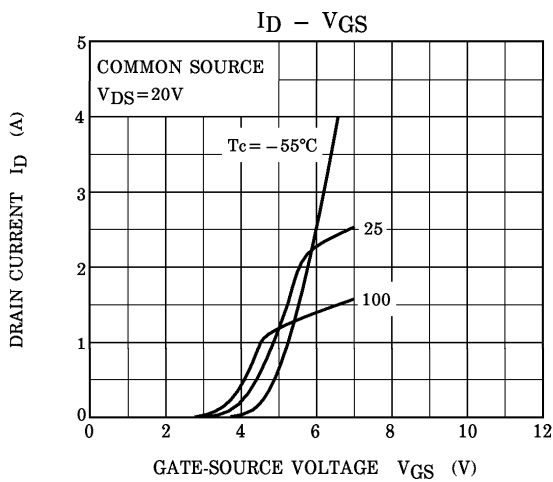
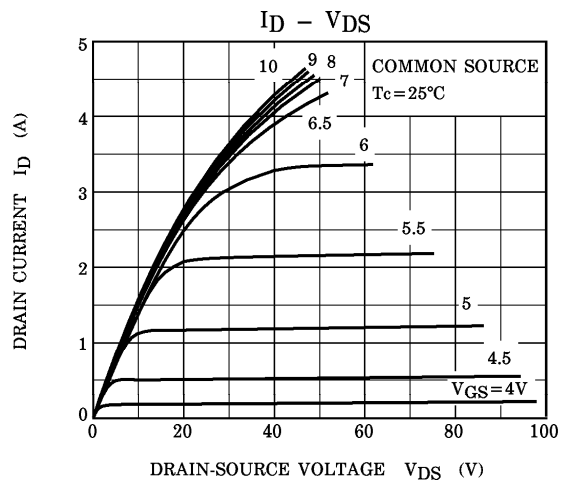
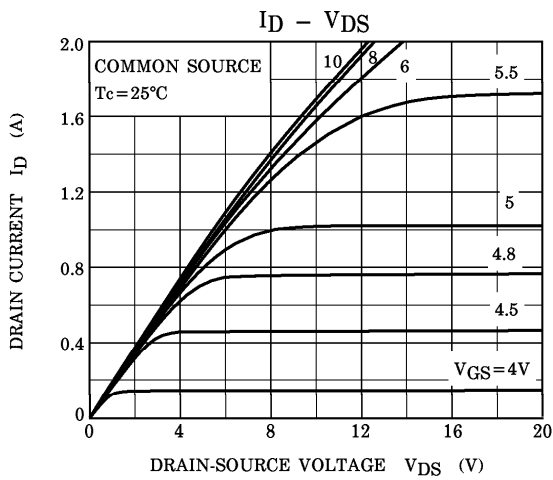
※ Lot Number

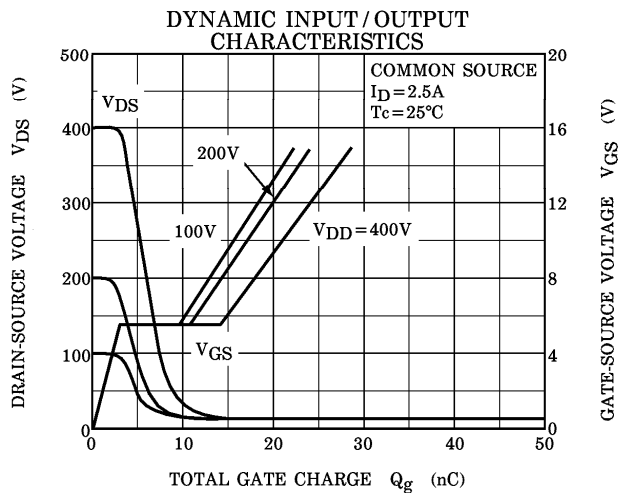
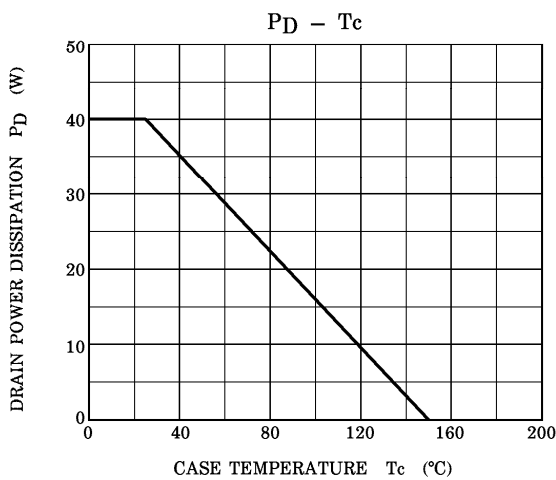
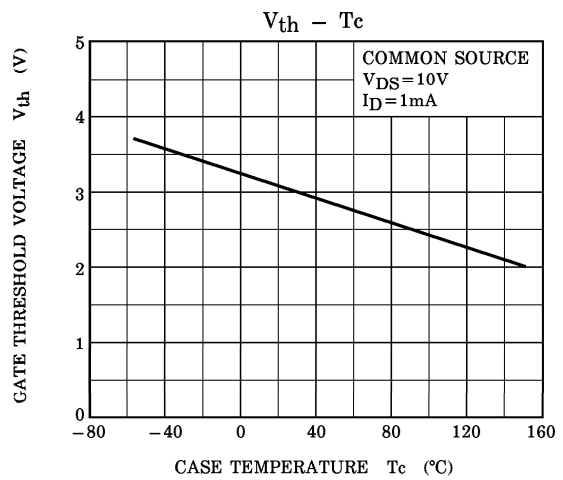
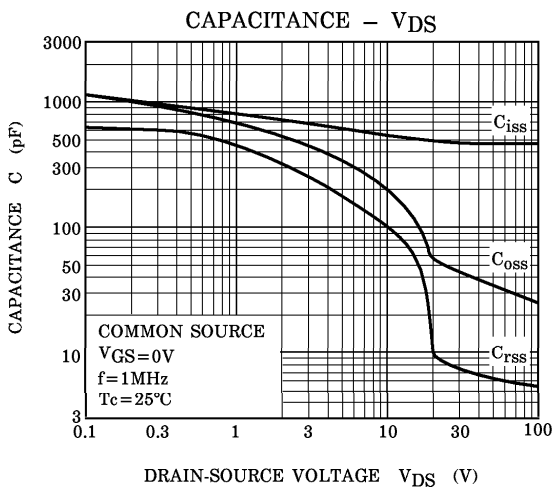
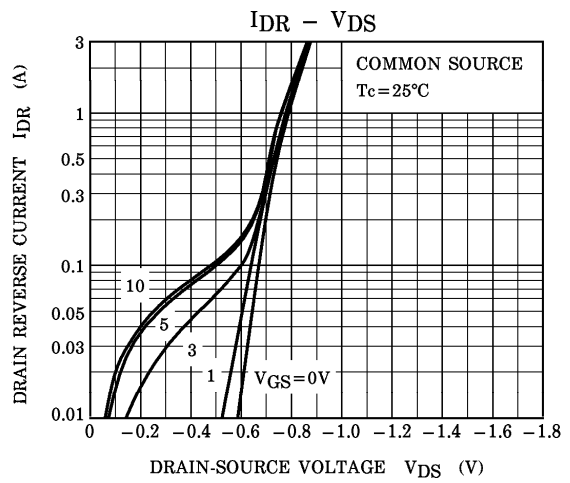
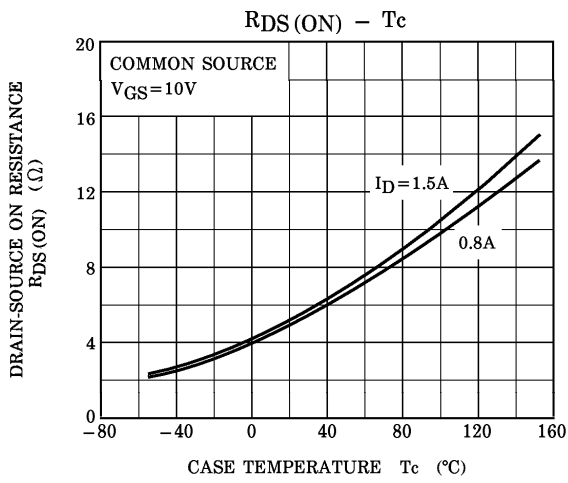


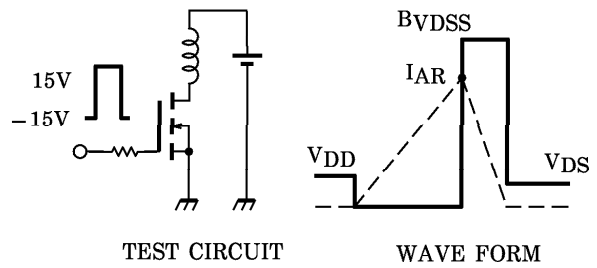
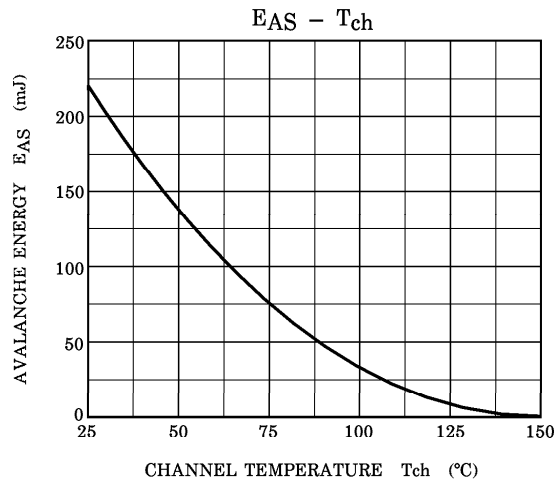
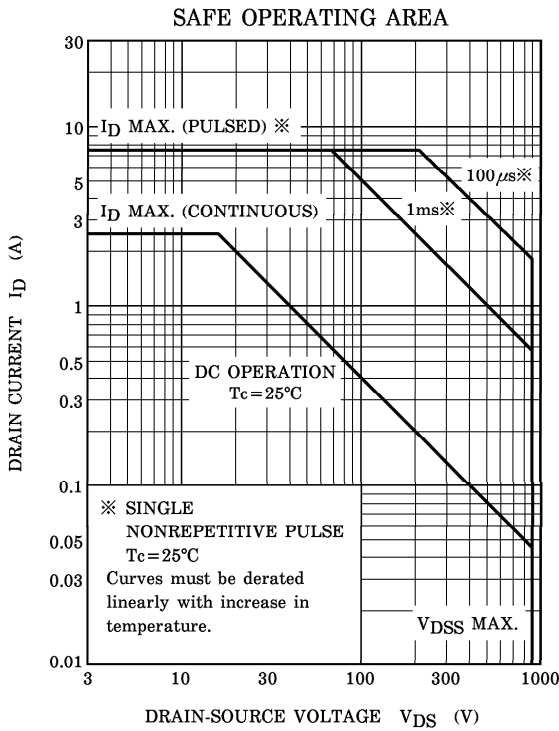
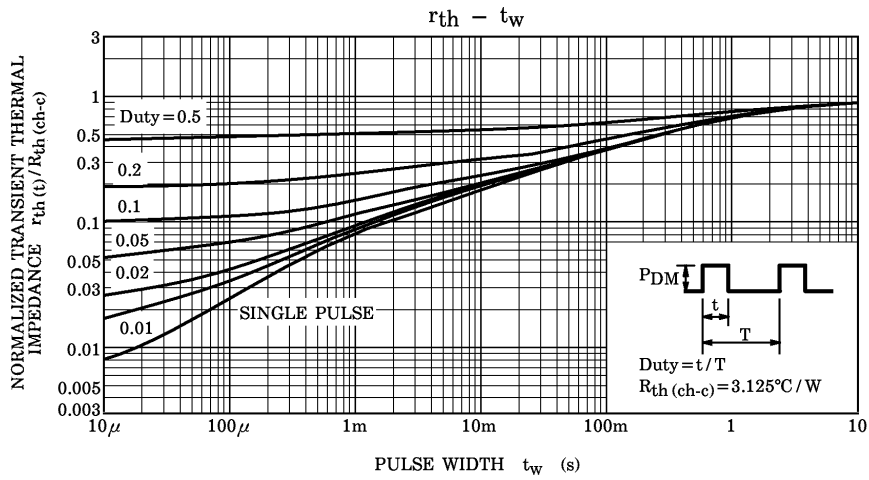
Month (Starting from Alphabet A)



Year (Last Number of the Christian Era)







Peak $I_{AR} = 2.5A$, $R_G = 25\Omega$, $V_{DD} = 90V$, $L = 63.4mH$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{BVDSS}{BVDSS - V_{DD}} \right)$$